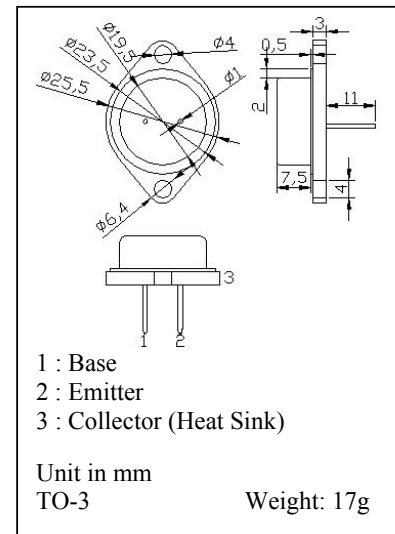


SILICON HIGH-POWER NPN TRANSISTOR

...designed for use in power switching circuits.
 ...designed for use in series and shunt regulators.
 ...designed for use in output stages and high fidelity amplifiers.

MAXIMUM RATINGS

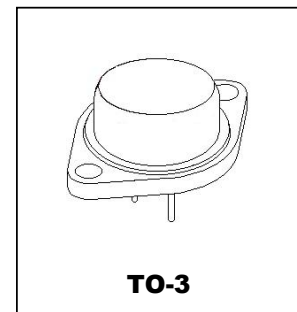
Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CB0}	100	V
Collector-Emitter Voltage	V _{CEO}	60	V
Emitter-Base Voltage	V _{EBO}	7	V
Collector Current	I _C	15	A
Base Current	I _B	7	A
Collector Power Dissipation (T _c =25°C)	P _C	115	W
Junction Temperature	T _j	200	°C
Storage Temperature Range	T _{stg}	-65~200	°C



ELECTRICAL CHARACTERISTICS (T_A = 25 °C unless otherwise noted)

Characteristic	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Collector Cut-off Current	I _{CEX}	V _{CB} =100V	-	-	1	mA
		V _{CE} =100V, T _j =150°C	-	-	5	mA
Collector Cut-off Current	I _{CEO}	V _{CB} =30V, I _B =0	-	-	0.7	mA
Emitter Cut-off Current	I _{EBO}	V _{EB} =7V, I _C =0	-	-	5	mA
DC Current Gain	h _{FE}	I _C =4A, V _{CE} =4V	20	-	70	-
		I _C =10A, V _{CE} =4V	5	-	-	-
Collector-Emitter Sustaining Voltage	V _{CEO(sus)}	I _C =200mA	60	-	-	V
Collector-Emitter Sustaining Voltage	V _{CEO(sus)}	I _C =200mA	70	-	-	V
Collector-Emitter Saturation Voltage	V _{CE(sat)}	I _C =4, I _B =400mA	-	-	1	V
		I _C =10, I _B =3.3A	-	-	3	V
Base-Emitter Voltage	V _{BE}	V _{CE} =4V, I _C =4A	-	-	1.8	V
Transition Frequency	f _T	V _{CE} =10V, I _C =0.5A	3	-	-	MHz

15 AMPERE
SILICON POWER TRANSISTORS



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